

10039284  
12/31/01

PATENT NUMBER and  
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10039284	12/31/2001	257			Go. Prat

\*\*APPLICANTS: Blanchard Richard; Hsieh Fwu-luan;

2811

\*\*CONTINUING DATA VERIFIED:

BEST AVAILABLE COPY

\*\* FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	ATTORNEY DOCKET NO
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no			GS 174
35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no			
Verified and Acknowledged Examiners's initials			
TITLE : High voltage power MOSFET having a voltage sustaining region that includes doped columns formed by trench etching using an etchant gas that is also a doping source			

U.S. DEPT. OF COMM. (PAT. & TM.-PTC-436) (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED		
			Total Claims	Print Claim for O.G.	
ISSUE FEE		Primary Examiner	DRAWING		
Amount Due	Date Paid		Sheets Drwg.	Figs. Drwg.	Print Fig.
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	Application Examiner		
WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.					

FILED WITH

☐ DISK (CRF)

☐ CD-ROM

(Attached in pocket on right inside flap)